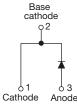
VS-HFA16TB120-M3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 16 A



www.vishay.com



PRIMARY CHARACTERISTICS							
I _{F(AV)} 16 A							
V _R	1200 V						
V _F at I _F	2.3 V						
t _{rr} typ.	30 ns						
T _J max.	150 °C						
Package TO-220AC 2L							
Circuit configuration	Single						

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- \bullet Designed and qualified according to ${\sf JEDEC}^{\circledast}{\sf -}{\sf JESD}$ 47



COMPLIANT

HALOGEN

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA16TB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	VR		1200	V				
Maximum continuous forward current	I _F	T _C = 100 °C	16					
Single pulse forward current	I _{FSM}		190	А				
Maximum repetitive forward current	I _{FRM}		64					
Movimum neuror discinction	P _D	T _C = 25 °C	151	14/				
Maximum power dissipation		T _C = 100 °C	60	W				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				

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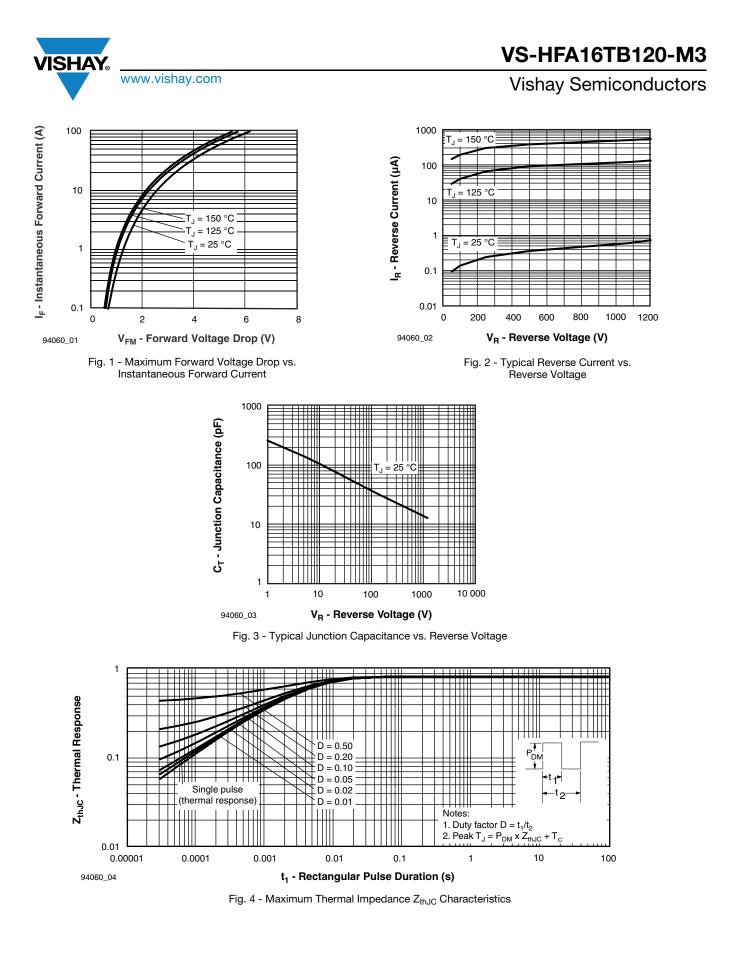
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ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-		
		I _F = 16 A		-	2.5	3.0	V	
Maximum forward voltage	V_{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93		
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7		
Maximum reverse		$V_R = V_R$ rated	Coofig 0	-	0.75	20		
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	375	2000	μA	
Junction capacitance	CT	V _R = 200 V See fig. 3		-	27	40	pF	
Series inductance	Ls	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ di}_F/\text{dt} = 200 $	A/μs, V _R = 30 V	-	30	-			
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	90	135	ns		
	t _{rr2}	T _J = 125 °C		-	164	245			
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 16 A	-	5.8	10	А		
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15	~		
Reverse recovery charge	Q _{rr1}	$T_J = 25 \ ^{\circ}C$	di _F /dt = 200 A/µs V _B = 200 V	-	260	675	nC		
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	680	1838			
Peak rate of fall of	di _{(rec)M} /dt1	T _J = 25 °C		-	120	-			
recovery current during t _b See fig. 8	di _{(rec)M} /dt2	T _J = 125 °C		-	76	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	0.83			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.50	-			
Weight			-	2.0	-	g		
weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style 2L TO-220AC		HFA16	STB120	•		



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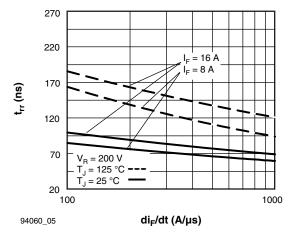


Fig. 5 - Typical Reverse Recovery Time vs. di_F/dt (Per Leg)

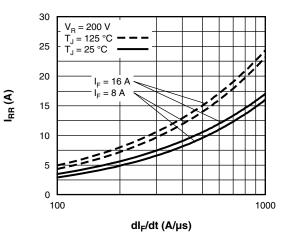


Fig. 6 - Typical Recovery Current vs. di_F/dt (Per Leg

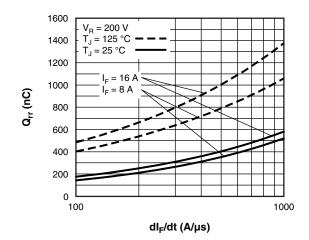


Fig. 7 - Typical Stored Charge vs. di_F/dt (Per Leg)

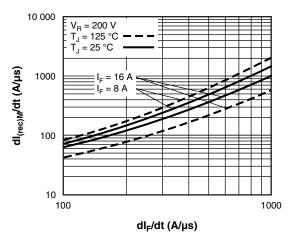


Fig. 8 - Typical $di_{(rec)M}/dt vs. di_F/dt$ (Per Leg)

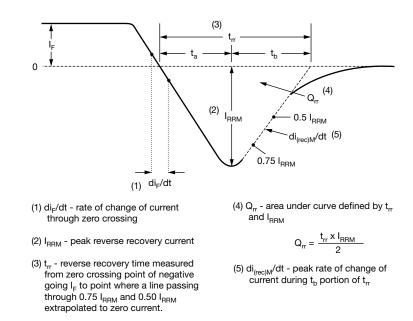


Fig. 9 - Reverse Recovery Waveform and Definitions

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VS-HFA16TB120-M3

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ORDERING INFORMATION TABLE

Device code	VS-	HF	А	16	тв	120	-M3
		2	3	4	5	6	7
	1 · · · · · · · · · · · · · · · · · · ·	- HEX - Elect - Cur - Pac TB	KFRED [®] ctron irra rent rati kage: = 2L TO	-	16 A)		
	7	- Env	ironmer	ntal digit gen-free	:		ant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-HFA16TB120-M3	50	Antistatic plastic tube					

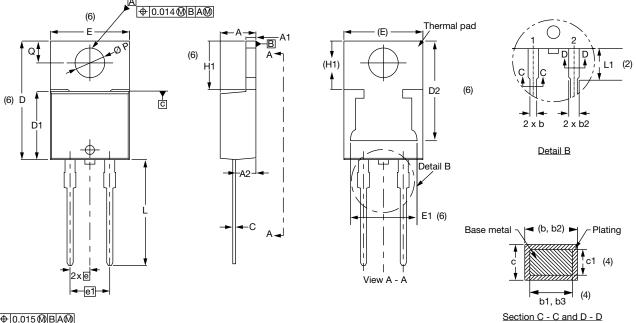
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96156				
Part marking information	www.vishay.com/doc?95391				



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TO-220AC 2L

DIMENSIONS in millimeters and inches



⊕0.015@BA@



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIBOL	MIN.	MAX. MIN.		MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
e	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Conforms to JEDEC[®] outline TO-220AC

Notes

⁽²⁾ Lead dimension and finish uncontrolled in L1

(4) Dimension b1, b3, and c1 apply to base metal only

- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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 $^{^{(1)}\,}$ Dimensioning and tolerancing as per ASME Y14.5M-1994 $\,$

⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁵⁾ Controlling dimensions: inches



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